VS-HFA30PB120HN3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 30 A



www.vishay.com

TO-247AC modified



PRODUCT SUMMARY						
Package	TO-247AC modified (2 pins)					
I _{F(AV)}	30 A					
V _R	1200 V					
V _F at I _F	2.3 V					
t _{rr} typ.	47 ns					
T _J max.	150 °C					
Diode variation	Single die					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- AEC-Q101 qualified, meets JESD 201 class 1A whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA30PB120... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		1200	V	
Maximum continuous forward current	I _F	T _C = 100 °C	30		
Single pulse forward current	I _{FSM}		120	А	
Maximum repetitive forward current	I _{FRM}		90		
Maximum power discipation	P _D	T _C = 25 °C	350	w	
Maximum power dissipation		T _C = 100 °C	140		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA		1200	-	-	
	V _{FM}	I _F = 30 A	See fig. 1	-	2.4	4.1	V
Maximum forward voltage		I _F = 60 A		-	3.1	5.7	
		$I_F = 30 \text{ A}, \text{ T}_J = 125 \text{ °C}$		-	2.3	4.0	
Maximum reverse		$V_{R} = V_{R}$ rated	Castin O		1.3	40	
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$ See fig. 2		-	1100	4000	μΑ
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	50	75	pF
Series inductance	L _S	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	47	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	I _F = 30 A dI _F /dt = 200 A/μs V _R = 200 V	-	110	170	ns
	t _{rr2}	T _J = 125 °C		-	170	260	
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C		-	10	15	_
	I _{RRM2}	T _J = 125 °C		-	16	24	~
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	650	980	
See fig. 7	Q _{rr2}	T _J = 125 °C		-	1540	2310	nc
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	270	-	A/ue
	dl _{(rec)M} /dt2	T _J = 125 °C		-	240	-	τνμs

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R _{thJC}		-	-	0.36		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	°C/W	
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-		
Woight			-	5.61	-	g	
weight			-	0.198	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style TO-247AC modified (JEDEC)		HFA30F	PB120H		

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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage









Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)



Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)



Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt(Per Leg)



Fig. 9 - Reverse Recovery Parameter Test Circuit

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I_{RRM} (A)

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Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA30PB120HN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95253					
Part marking information	www.vishay.com/doc?95442					
SPICE model	www.vishay.com/doc?95358					

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DIMENSIONS in millimeters and inches



Section C - C, D - D, E - E

(4)

(b b2 b4)

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View B

SVMPOL	MILLIMETERS		INC	NOTES	
STNIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMPOL	MILLIMETERS		INC	INCHES		
STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
D2	0.51	1.30	0.020	0.051		
E	15.29	15.87	0.602	0.625	3	
E1	13.46	-	0.530	-		
е	5.46 BSC		0.215	BSC		
ØК	0.2	0.254		0.010		
L	14.20	16.10	0.559	0.634		
L1	3.71	4.29	0.146	0.169		
ØP	3.56	3.66	0.14	0.144		
Ø P1	-	6.98	-	0.275		
Q	5.31	5.69	0.209	0.224		
R	4.52	5.49	0.178	0.216		
S	5.51	BSC	0.217 BSC			

Notes

- ⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension c

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